

| L Number | Hits | Search Text | DB | Time stamp |
|----------|---------|--|--------------------|---------------------|
| 13 | 3381 | ((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS. | USPAT; US-PGPUB | 2004/04/15 13:50 |
| 14 | 743 | LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor" | USPAT; US-PGPUB | 2004/04/15 13:51 |
| 15 | 1416 | RSD or "reduced surface drain" or "reduced-surface-drain" | USPAT; US-PGPUB | 2004/04/15 13:51 |
| 16 | 9 | (LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor") and (RSD or "reduced surface drain" or "reduced-surface-drain") | USPAT; US-PGPUB | 2004/04/15 13:51 |
| 17 | 1 | ((((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and ((LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor") and (RSD or "reduced surface drain" or "reduced-surface-drain")) | USPAT; US-PGPUB | 2004/04/15 13:51 |
| 18 | 9 | ((((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and (RSD or "reduced surface drain" or "reduced-surface-drain") | USPAT; US-PGPUB | 2004/04/15 13:55 |
| 19 | 34 | ((((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and (LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor") | USPAT; US-PGPUB | 2004/04/15 13:55 |
| 20 | 3404420 | @ad<20010821 | USPAT; US-PGPUB | 2004/04/15 13:56 |
| 21 | 28 | (((((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and (LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor")) and @ad<20010821 | USPAT; US-PGPUB | 2004/04/15 14:05 |
| 23 | 1160 | (implant or implants or implanted or implanting or implantation) with (heat or heats or heated or heating or anneal or anneals or annealed or annealing) with ((dielectric or dielectrics or insulating or insulatings or oxide or oxides) with (gate or gates)) | USPAT; US-PGPUB | 2004/04/15 14:08 |

| | | | | |
|----|-----|--|--------------------|---------------------|
| 24 | 204 | ((((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and ((implant or implants or implanted or implanting or implantation) with (heat or heats or heated or heating or anneal or anneals or annealed or annealing) with ((dielectric or dielectrics or insulating or insulating or oxide or oxides) with (gate or gates)))) | USPAT; US-PGPUB | 2004/04/15 14:09 |
| 25 | 1 | (((((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and (LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor")) and @ad<20010821) and (((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and ((implant or implants or implanted or implanting or implantation) with (heat or heats or heated or heating or anneal or anneals or annealed or annealing) with ((dielectric or dielectrics or insulating or insulating or oxide or oxides) with (gate or gates)))) | USPAT; US-PGPUB | 2004/04/15 14:10 |
| 26 | 911 | ((implant or implants or implanted or implanting or implantation) with (heat or heats or heated or heating or anneal or anneals or annealed or annealing) with ((dielectric or dielectrics or insulating or insulating or oxide or oxides) with (gate or gates))) and @ad<20010821 | USPAT; US-PGPUB | 2004/04/15 14:11 |
| 27 | 9 | (RSD or "reduced surface drain" or "reduced-surface-drain") and ((LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor") and (RSD or "reduced surface drain" or "reduced-surface-drain")) | USPAT; US-PGPUB | 2004/04/15 14:11 |
| 28 | 0 | ((implant or implants or implanted or implanting or implantation) with (heat or heats or heated or heating or anneal or anneals or annealed or annealing) with ((dielectric or dielectrics or insulating or insulating or oxide or oxides) with (gate or gates))) and @ad<20010821) and ((RSD or "reduced surface drain" or "reduced-surface-drain") and ((LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor") and (RSD or "reduced surface drain" or "reduced-surface-drain")) | USPAT; US-PGPUB | 2004/04/15 14:11 |

| | | | | |
|----|-----|--|--------------------|---------------------|
| 29 | 173 | @ad<20010821 and (((((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and ((implant or implants or implanted or implanting or implantation) with (heat or heats or heated or heating or anneal or anneals or annealed or annealing) with ((dielectric or dielectrics or insulating or insulating or oxide or oxides) with (gate or gates)))))) | USPAT; US-PGPUB | 2004/04/15 14:12 |
|----|-----|--|--------------------|---------------------|